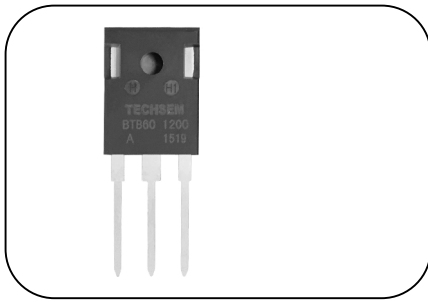


**Features:**

- Two anti-paralled thyristors on one
- Si-wafer
- Hermetic metal cases with ceramic

Typical Applications

- High power industrial and power transmissior
- DC and AC motor control
- AC controllers

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T _j (C)	VALUE			UNIT
				Min	Type	Max	
I _{T(RMS)}	RMS current	full sine wave Single side cooled, T _C =75°C	125			60	A
V _{DRM} V _{RRM}	Repetitive peak reverse voltage	V _{DRM} tp=10ms V _{DSM} = V _{DRM} +100V	125	800		1800	V
I _{DRM} I _{RRM}	Repetitive peak current	V _{DM} = V _{DRM}	125			0.8	mA
I _{TSM}	Surge on-state current	10ms half sine wave	125			600	A
I ² t	I ² T for fusing coordination	V _R =0.6V _{RRM}				1800	A ² s
V _{TM}	Peak on-state voltage	I _{TM} =90A, tp=10ms	25			1.65	V
dv/dt	Critical rate of rise of off-state voltage	V _{DM} =0.67V _{DRM} gate open	125	1000			V/μs
di/dt	Critical rate of rise of on-state current		125	20			A/μs
I _{GT}	Gate trigger current	V _D =12V _{DC} , R _L =33Ω I - II -III	25			50	mA
V _{GT}	Gate trigger voltage					1.3	V
I _H	Holding current					60	mA
I _{GM}	Peak gate current	tp=20μs	125			8	A
P _{GM}	Peak gate power	tp=20μs	125			10	w
P _{G(AV)}	Average gate power dissipation		125			2	w
R _{th(j-c)}	Thermal resistance Junction to case	Single side cooled				0.45	C /W
R _{th(j-a)}	Thermal resistance Junction to ambient					40	
T _j	Operating Junction temperature			-40		125	
T _{stg}	Stored temperature	単位 mm		-40		150	C
Outline	TO-247AA						

Outline: